

HiPerFET™ **Power MOSFETs Q-CLASS**

IXFX 90N20Q IXFK 90N20Q

200 90 $22 \text{ m}\Omega$ $\boldsymbol{R}_{\text{DS(on)}}$

 $t_{rr} \le 200 \; \mu s$

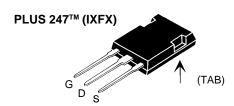
Single MOSFET Die

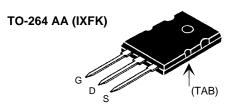
N-Channel Enhancement Mode Avalanche Rated, Low Qg, High dV/dt, Low t,,



Symbol	Test Conditions	Maximum Rating	
V _{DSS}	$T_J = 25$ °C to 150°C $T_J = 25$ °C to 150°C; $R_{GS} = 1$ MΩ	200 200	V
V _{GS} V _{GSM}	Continuous Transient	±20 ±30	V
D _{D25}	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 25^{\circ}{\rm C}$, pulse width limited by $T_{\rm JM}$ $T_{\rm C} = 25^{\circ}{\rm C}$	90 360 90	A A A
E _{AR} E _{AS}	T _c = 25°C T _c = 25°C	60 2.5	mJ J
dv/dt	$I_{_{S}} \leq I_{_{DM}}$, di/dt \leq 100 A/ μ s, $V_{_{DD}} \leq V_{_{DSS}}$ $T_{_{J}} \leq$ 150°C, $R_{_{G}} = 2 \Omega$	5	V/ns
$\overline{\mathbf{P}_{_{\mathrm{D}}}}$	T _C = 25°C	500	W
		-55 + 150	°C
T _{JM} T _{stg}		150 -55 +150	°C °C
T _L	1.6 mm (0.063 in.) from case for 10 s	300	°C
M_d	Mounting torque TO-264	0.4/6 N	m/lb.in.
Weight	PLUS 247 TO-264	6 10	g g

Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified) min. typ. max.		
$\overline{\mathbf{V}_{\mathtt{DSS}}}$	V _{GS} = 0 V, I _D = 250uA	200	,,,	V
V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 4mA$	2.0		4.0 V
I _{gss}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$			±100 nA
I _{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 V$	T _J = 125°C		100 μA 2 mA
R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_{D} = 0.5 \bullet I_{D25}$ Note 1			22 mΩ





G = Gate	D = Drain
S = Source	TAB = Drain

Features

- IXYS advanced low Q process
- Low gate charge and capacitances
 - easier to drive
 - faster switching
- International standard packages
- Low R_{DS (on)}
 Rated for unclamped Inductive load switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

Applications

- DC-DC converters
- · Battery chargers
- Switched-mode and resonant-mode power supplies
- · DC choppers
- · AC motor control
- · Temperature and lighting controls

Advantages

- PLUS 247[™] package for clip or spring mounting
- Space savings
- · High power density



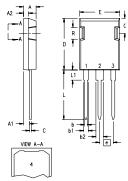
Symbol	Test Conditions	Characteristic Values (T ₁ = 25°C, unless otherwise specified)				
	`	J ,	min.		max.	
g_{fs}	$V_{DS} = 10 \text{ V}; I_{D} = 0.5 \cdot I_{D25}$ No	ote 1	40	50		S
C _{iss})			6800		рF
C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 0$	1 MHz		1620		pF
\mathbf{C}_{rss}	J			480		pF
t _{d(on)})			35		ns
t _r	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \bullet V_{DS}$	$I_D = 0.5 \bullet$	D25	31		ns
$\mathbf{t}_{d(off)}$	$R_{\rm G} = 1 \Omega \text{ (External)},$			82		ns
t _f)			12		ns
Q _{g(on)})			190		nC
\mathbf{Q}_{gs}	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \cdot V_{DS}$	$I_D = 0.5 \bullet$	D ₂₅	40		nC
\mathbf{Q}_{gd}	J			90		nC
R _{thJC}					0.26	K/W
R _{thCK}				0.15		K/W

Source-Drain Diode

Symbol	Test Conditions min.	typ.	max.	
I _s	V _{GS} = 0 V		90	Α
I _{sm}	Repetitive; pulse width limited by $T_{_{\rm JM}}$		360	A
$\mathbf{V}_{\mathtt{SD}}$	$I_F = I_S$, $V_{GS} = 0$ V, Note 1		1.3	V
t _{rr})		200	ns
$\mathbf{Q}_{_{\mathbf{RM}}}$	$I_F = 45A, -di/dt = 100 A/\mu s, V_R = 100 V$	1.4		μС
I _{RM}	J	10		Α

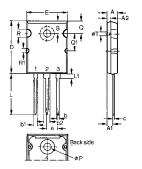
Note: 1. Pulse test, $t \le 300 \ \mu s$, duty cycle $d \le 2 \ \%$

PLUS247™ (IXFX) Outline



Dim.	Mill	imeter	Inches		
	Min.	Max.	Min.	Max.	
Α	4.83	5.21	.190	.205	
A,	2.29	2.54	.090	.100	
A_2	1.91	2.16	.075	.085	
b	1.14	1.40	.045	.055	
b₁	1.91	2.13	.075	.084	
b ₂	2.92	3.12	.115	.123	
С	0.61	0.80	.024	.031	
D	20.80	21.34	.819	.840	
Е	15.75	16.13	.620	.635	
е	5.45 BSC		.215 BSC		
L	19.81	20.32	.780	.800	
L1	3.81	4.32	.150	.170	
Q	5.59	6.20	.220	.244	
R	4.32	4.83	.170	.190	

TO-264 AA Outline



Dim.	Millimeter		limeter Inche	
	Min.	Max.	Min.	Max.
Α	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
С	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
е	5.46BSC		.215BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
Р	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
Т	1.57	1.83	.062	.072

